

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

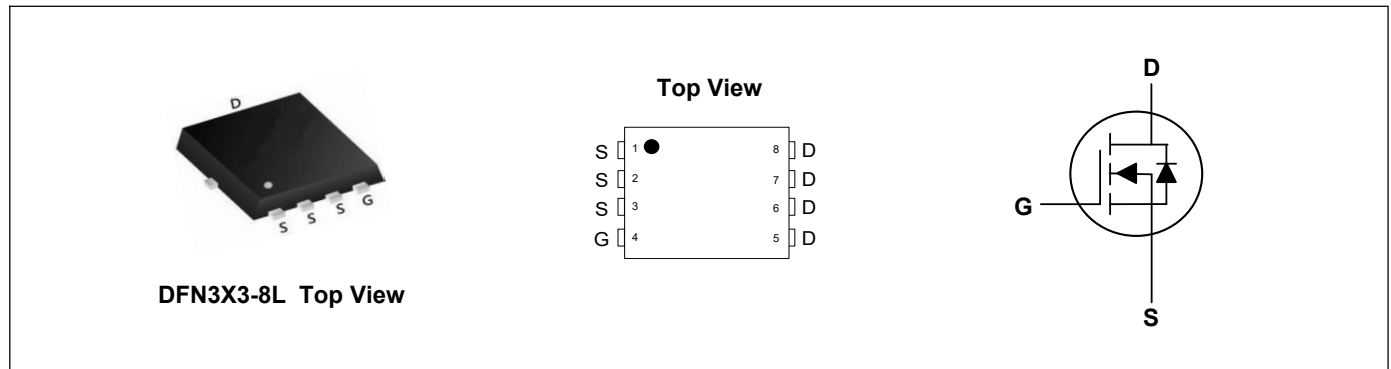
Product Summary



V_{DS}	30	V
I_D	80	A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	4	m Ω
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	6	m Ω

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch



Absolute Maximum Ratings($T_C=25^{\circ}C$, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current, $V_{GS} @ 10V^1$	$I_D @ T_C=25^{\circ}C$	80	A
Continuous Drain Current, $V_{GS} @ 10V^1$	$I_D @ T_C=100^{\circ}C$	50	A
Continuous Drain Current, $V_{GS} @ 10V^1$	$I_D @ T_A=25^{\circ}C$	17	A
Continuous Drain Current, $V_{GS} @ 10V^1$	$I_D @ T_A=70^{\circ}C$	14	A
Pulsed Drain Current ²	I_{DM}	160	A
Single Pulse Avalanche Energy ³	EAS	144.7	mJ
Avalanche Current	I_{AS}	53.8	A
Total Power Dissipation ⁴	$P_D @ T_C=25^{\circ}C$	43.4	W
Total Power Dissipation ⁴	$P_D @ T_A=25^{\circ}C$	1.67	W
Storage Temperature Range	T_{STG}	-55 to 150	$^{\circ}C$
Operating Junction Temperature Range	T_J	-55 to 150	$^{\circ}C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Ambient ¹	$R_{\theta JA}$	---	75	$^{\circ}C/W$
Thermal Resistance Junction-Case ¹	$R_{\theta JC}$	---	2.88	$^{\circ}C/W$

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	30	---	---	V
BV _{DSS} Temperature Coefficient	ΔBV _{DSS} /ΔT _J	Reference to 25°C, I _D =1mA	---	0.0213	---	V/°C
Static Drain-Source On-Resistance ²	R _{DS(ON)}	V _{GS} =10V, I _D =30A	---	---	4	mΩ
		V _{GS} =4.5V, I _D =15A	---	---	6	mΩ
Gate Threshold Voltage	V _{GS(th)}	V _{GS} =V _{DS} , I _D =250uA	1.0	---	2.5	V
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)}		---	-5.73	---	mV/°C
Drain-Source Leakage Current	I _{DSS}	V _{DS} =24V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =24V, V _{GS} =0V, T _J =55°C	---	---	5	
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
Forward Transconductance	g _{fs}	V _{DS} =5V, I _D =30A	---	26.5	---	S
Gate Resistance	R _g	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	1.4	---	Ω
Total Gate Charge (4.5V)	Q _g	V _{DS} =20V, V _{GS} =4.5V, I _D =12A	---	31.6	---	nC
Gate-Source Charge	Q _{gs}		---	6.07	---	
Gate-Drain Charge	Q _{gd}		---	13.8	---	
Turn-On Delay Time	T _{d(on)}	V _{DD} =15V, V _{GS} =10V, R _G =1.5Ω, I _D =20A	---	11.2	---	ns
Rise Time	T _r		---	49	---	
Turn-Off Delay Time	T _{d(off)}		---	35	---	
Fall Time	T _f		---	7.8	---	
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	3075	---	pF
Output Capacitance	C _{oss}		---	400	---	
Reverse Transfer Capacitance	C _{rss}		---	315	---	

Drain-Source Diode Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Continuous Source Current ^{1,5}	I _S	V _G =V _D =0V, Force Current	---	---	80	A
Pulsed Source Current ^{2,5}	I _{SM}		---	---	160	A
Diode Forward Voltage ²	V _{SD}	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1	V

Note:

- The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- The EAS data shows Max. rating. The test condition is V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=53.8A
- The power dissipation is limited by 150°C junction temperature
- The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

Typical Characteristics

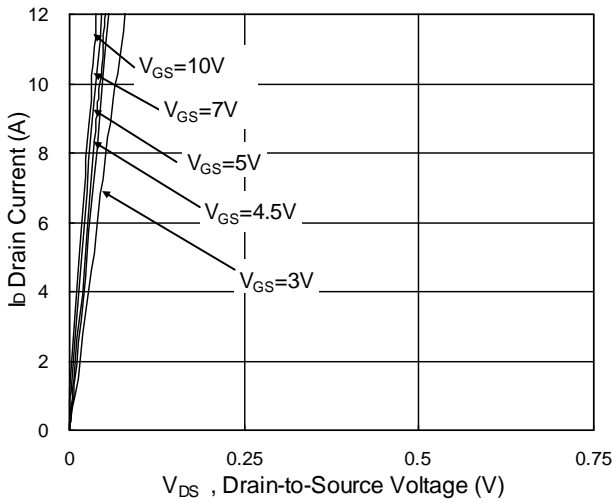


Fig.1 Typical Output Characteristics

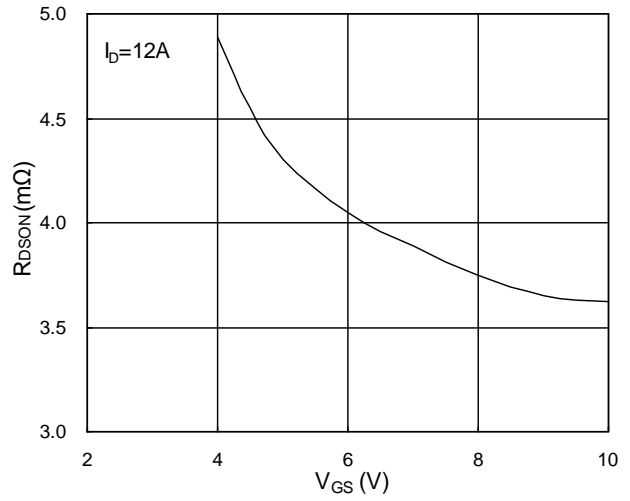


Fig.2 On-Resistance vs. G-S Voltage

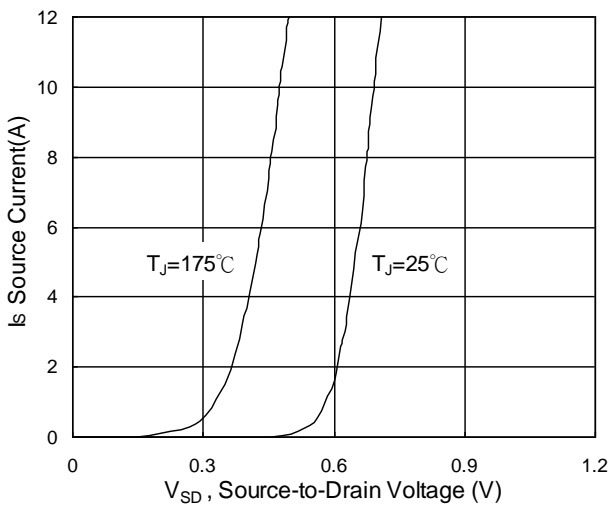


Fig.3 Forward Characteristics of Reverse

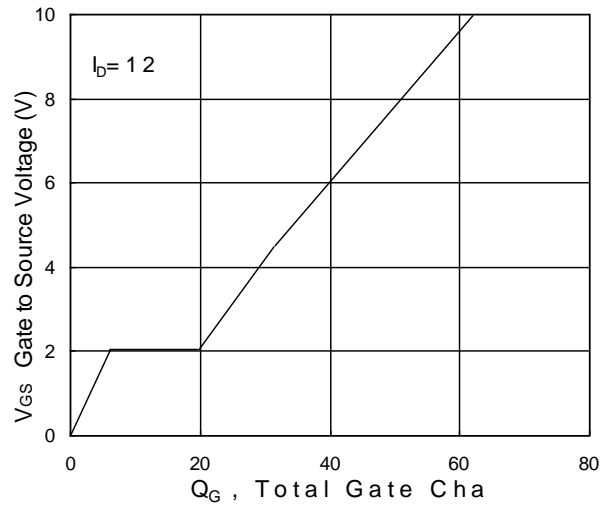


Fig.4 Gate-Charge Characteristics

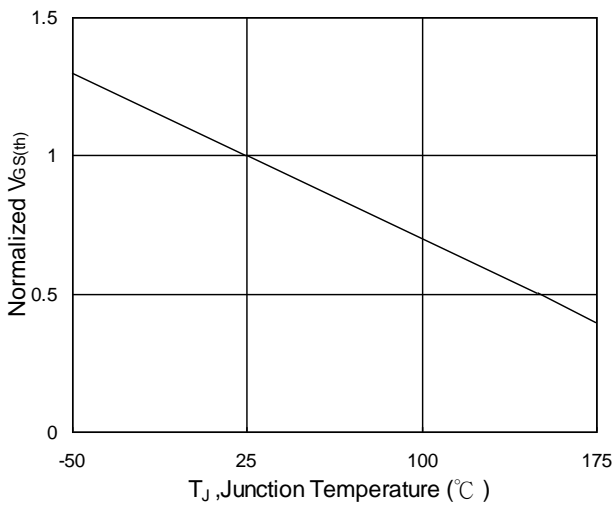


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

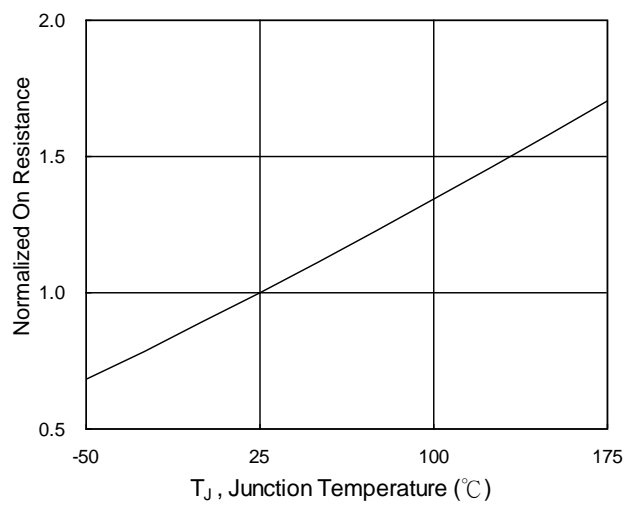


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

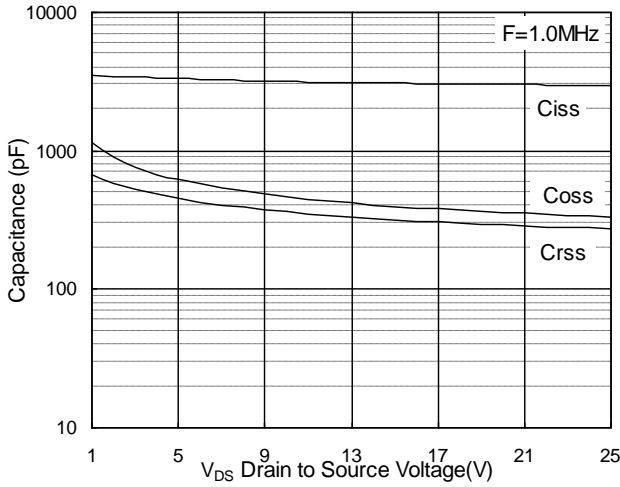


Fig.7 Capacitance

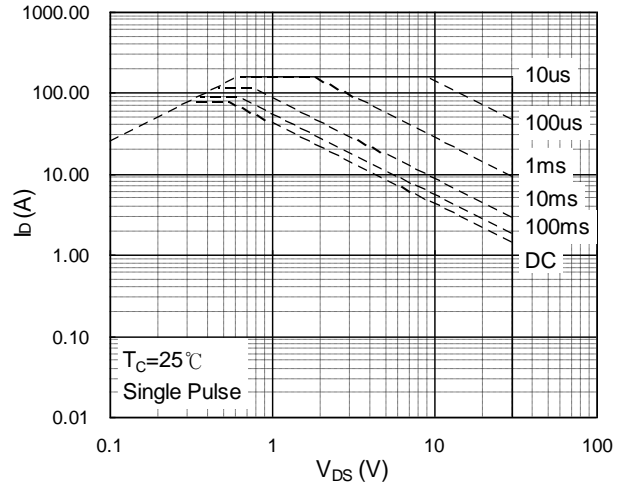


Fig.8 Safe Operating Area

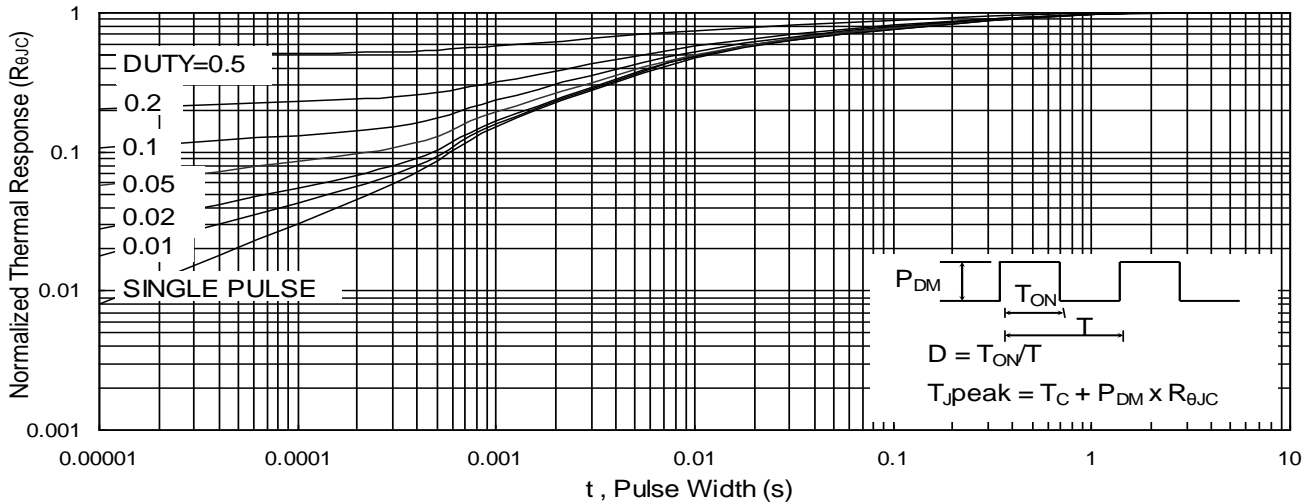


Fig.9 Normalized Maximum Transient Thermal Impedance

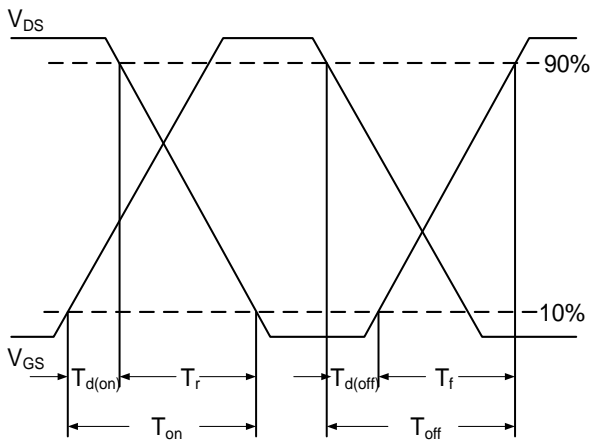


Fig.10 Switching Time Waveform

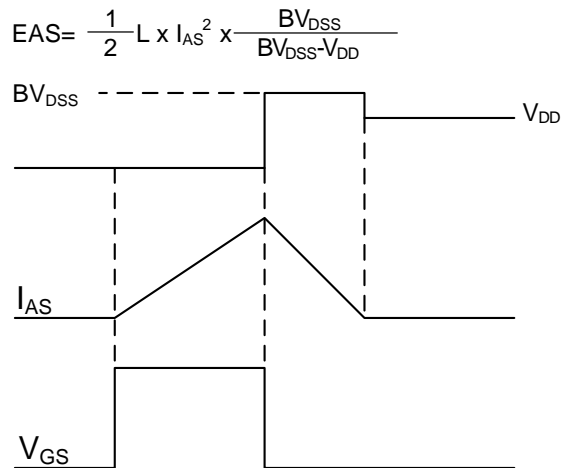
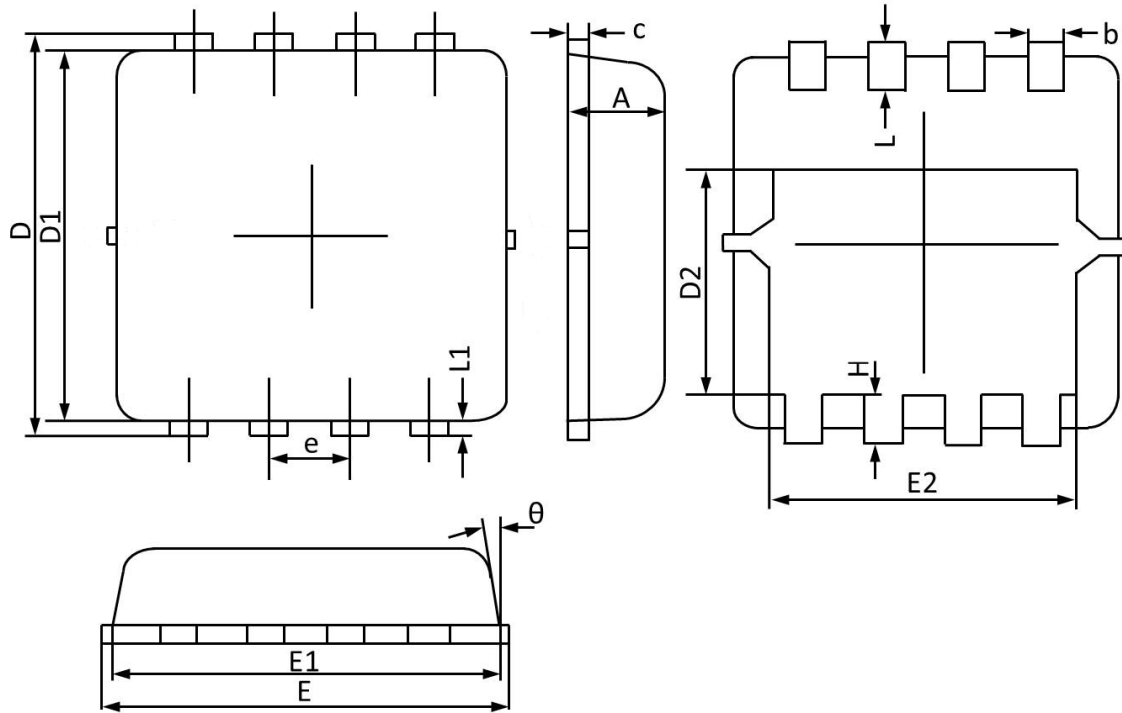


Fig.11 Unclamped Inductive Switching Waveform

DFN3X3-8L Package Outline Dimensions



Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	0.70	0.75	0.85	E1	2.90	3.10	3.25
b	0.24	0.30	0.35	E2	2.35	2.50	2.60
c	0.10	0.17	0.25	e	0.65 BSC		
D	3.10	3.30	3.45	H	0.30	0.40	0.50
D1	2.90	3.05	3.20	L	0.30	0.40	0.50
D2	1.45	1.70	1.95	L1	--	0.13	--
E	3.05	3.25	3.40	theta	0°		14°